1. General description

NPN high-voltage low V_{CEsat} transistor in a SOT89 (SC-62) medium power and flat lead Surface-Mounted Device (SMD) plastic package.

PNP complement: PBHV9040X

2. Features and benefits

- · High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain h_{FE} at high I_C
- AEC-Q101 qualified

3. Applications

- LED driver for LED chain module
- LCD backlighting
- · Automotive motor management
- · Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V	-	-	500	V
V_{CEO}	collector-emitter voltage	open base	-	-	400	V
I _C	collector current		-	-	0.5	Α
h _{FE}	DC current gain	$V_{CE} = 10 \text{ V}; I_{C} = 50 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	100	200	-	



500 V, 0.5 A NPN high-voltage low VCEsat transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		С
2	С	collector		B .
3	В	base	3 2 1	B — E sym042
			SOT89	sy

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBHV8540X	SOT89	plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	SOT89			

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBHV8540X	%4D

[1] % = placeholder for manufacturing site code

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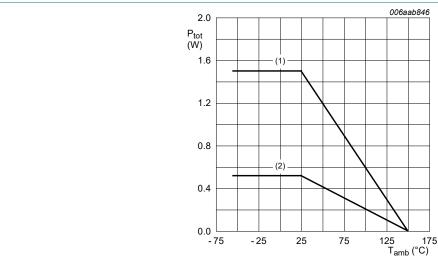
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	500	V
V _{CEO}	collector-emitter voltage	open base		-	400	V
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V		-	500	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current			-	0.5	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	1	Α
I _{BM}	peak base current			-	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.52	W
			[2]	-	1.5	W
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².



- (1) FR4 PCB, mounting pad for collector 6 cm²
- (2) FR4 PCB, standard footprint

Fig. 1. Power derating curves

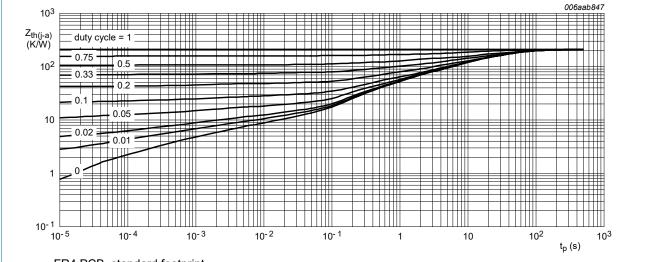
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9. Thermal characteristics

Table 6. Thermal characteristics

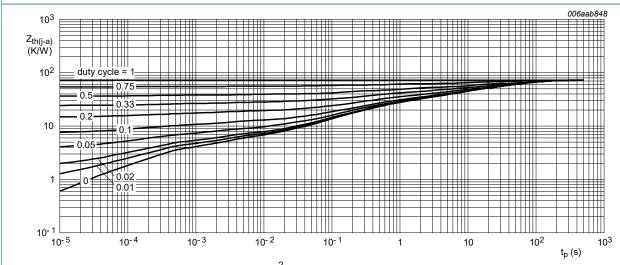
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	-	240	K/W
	junction to ambient		[2]	-	-	83	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².



FR4 PCB, standard footprint

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for collector 6 cm²

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

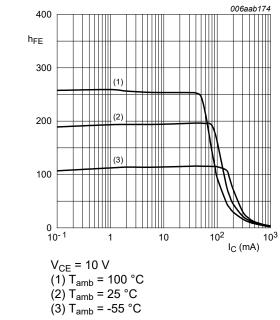
500 V, 0.5 A NPN high-voltage low VCEsat transistor

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 320 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 320 V; I _E = 0 A; T _j = 150 °C	-	-	10	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 4 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
I _{CES}	collector-emitter cut-off current	V _{CE} = 320 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 10 V; I _C = 50 mA; T _{amb} = 25 °C	100	200	-	
		V_{CE} = 10 V; I_{C} = 100 mA; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C; pulsed	80	150	-	
		V_{CE} = 10 V; I_{C} = 300 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	10	20	-	
V _{CEsat}	collector-emitter	I _C = 100 mA; I _B = 10 mA; T _{amb} = 25 °C	-	100	200	mV
	saturation voltage	I _C = 100 mA; I _B = 20 mA; T _{amb} = 25 °C	-	60	90	mV
		I _C = 300 mA; I _B = 60 mA; T _{amb} = 25 °C	-	135	250	mV
V _{BEsat}	base-emitter saturation voltage	I_C = 300 mA; I_B = 60 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.91	1.1	V
t _d	delay time	V _{CC} = 6 V; I _C = 0.5 A; I _{Bon} = 0.1 A;	-	50	-	ns
t _r	rise time	I _{Boff} = -0.1 A; T _{amb} = 25 °C	-	6200	-	ns
t _{on}	turn-on time		-	6250	-	ns
t _s	storage time		-	800	-	ns
t _f	fall time		-	2200	-	ns
t _{off}	turn-off time		-	3000	-	ns
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 100 mA; f = 100 MHz; T_{amb} = 25 °C	-	30	-	MHz
C _c	collector capacitance	$V_{CB} = 20 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 ^{\circ}\text{C}$	-	4	-	pF
C _e	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_{C} = 0 \text{ A}; i_{c} = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 \text{ °C}$	-	165	-	pF

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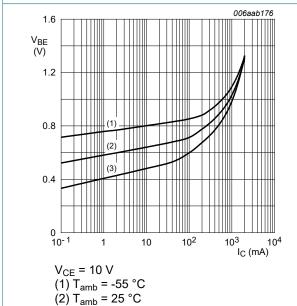
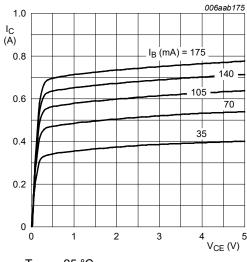


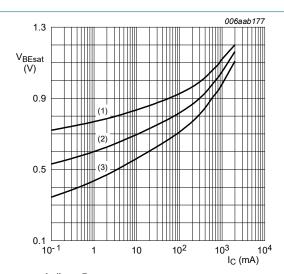
Fig. 6. Base-emitter voltage as a function of collector current; typical values

(3) $T_{amb} = 100 \, ^{\circ}C$



 T_{amb} = 25 °C

Fig. 5. Collector current as a function of collectoremitter voltage; typical values



 $I_C/I_B = 5$

(1) $T_{amb} = -55$ °C (2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

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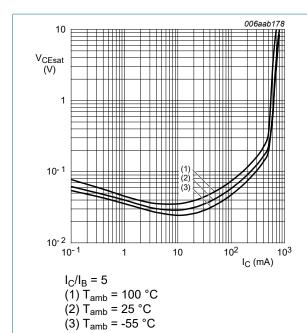


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

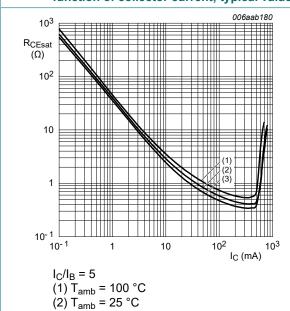


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

(3) $T_{amb} = -55 \, ^{\circ}C$

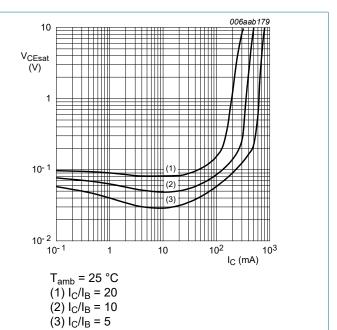


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

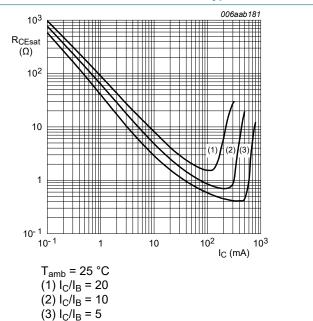
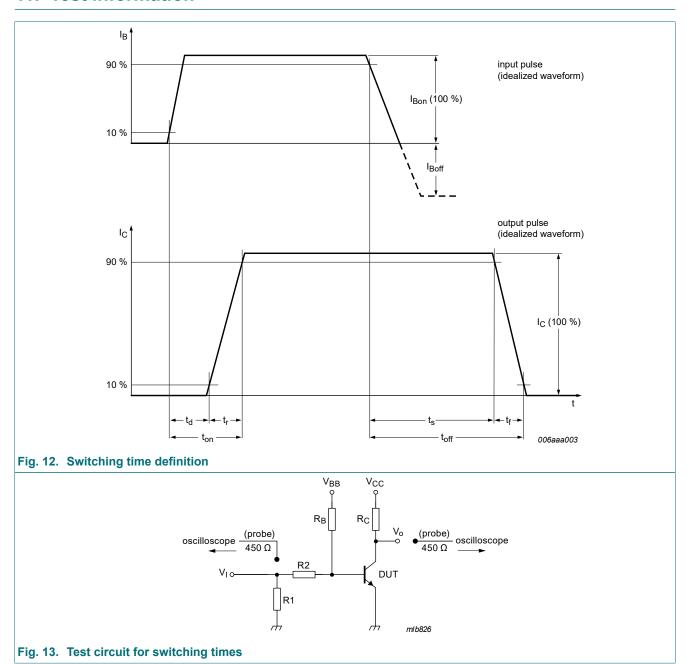


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

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11. Test information

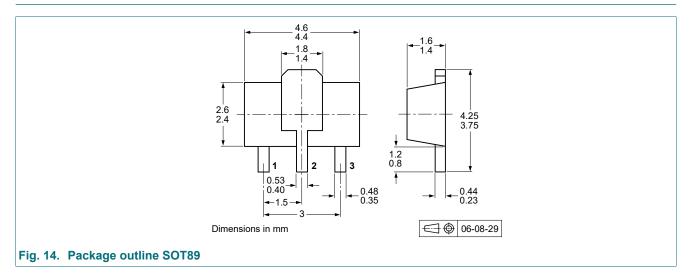


Quality information

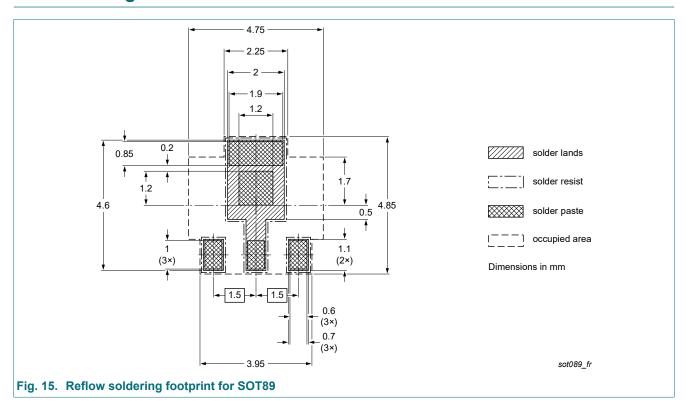
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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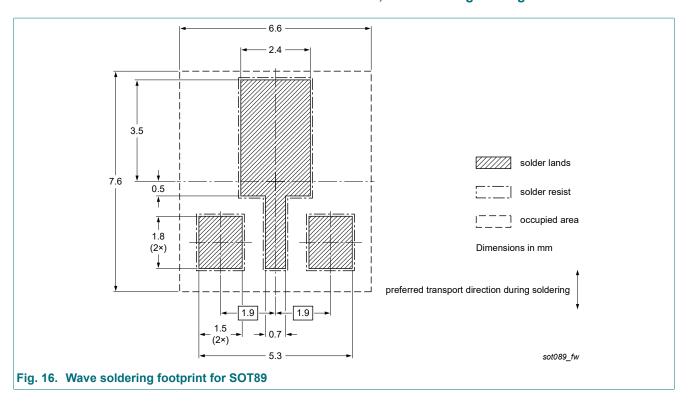
12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PBHV8540X v.2	20230712	Product data sheet	-	PBHV8540X v.1			
Modifications:	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. 						
PBHV8540X v.1	20131205	Product data sheet	-	-			

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 12 July 2023

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